

EAST Search History

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	43	((arup near1 bhattacharyya).in. micron. as.) and (CMOS CMOSFET SRAM invert? r).ti,ab,clm. and (field adj effect adj transistor FET) and (stack\$3 pillar) and (Si silicon).clm. and (Ge germanium). clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 15:43
L2	0	((arup near1 bhattacharyya).in. micron. as.) and (CMOS CMOSFET SRAM invert? r).clm. and (field adj effect adj transistor FET).clm. and (stack\$3 pillar column "via").clm. and (Si silicon).clm. and (Ge germanium).clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 15:44
L3	41	((arup near1 bhattacharyya).in. micron. as.) and (CMOS CMOSFET SRAM invert? r).clm. and (field adj effect adj transistor FET).clm. and (stack\$3 pillar column "via").clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 15:44
S1	4	"264914".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/08/20 09:44
S2	6	"760087".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26
S3	3	("6808971").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 06:26
S4	1	"6429085".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:27
S5	1	"5006913".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:42
S6	1	"4768076".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:43
S7	1	"4692994".PN.	USPAT; USOCR	OR	OFF	2005/09/07 06:44
S8	8	((("4692994") or ("4768076") or ("5006913") or ("6429085"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 07:44
S9	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2005/09/07 07:45
S10	0	battacharyya.in. and strained and (sige gesi si-ge ge-si silicon adj germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56

S11	0	battacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:56
S12	644	bhattacharyya.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57
S13	73	bhattacharyya.in. and cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 08:57
S14	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:57
S15	36	bhattacharyya.in. and cmos and (thin adj film TFT) and strained and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 08:58
S16	35	bhattacharyya.in. and cmos and (thin adj film TFT) and strained.clm. and (sige gesi si-ge ge-si silicon adj germanium germanium adj silicon).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:17
S17	11	(inverter invertor).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si. sub."\$4 near1 "Ge.sub."\$4 "Si. sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si. sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti,ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:24
S18	11	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si. sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si. sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti,ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and (thin adj film adj transistor tft)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26
S19	34	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si. sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si. sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti,ab,clm. and (monocrystalline single adj crystal).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 09:26
S20	5	(inverter invertor CMOS).ti,ab,clm. and ((silicon near1 germanium) (si near1 ge) ("Si.sub."\$4 near1 "Ge.sub."\$4 "Si. sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si. sub."\$4 Si-Ge Ge-Si)).ti,ab,clm. and strained.ti,ab,clm. and (monocrystalline single adj crystal).ti,ab,clm. and @ad< "20020311"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 10:33

S21	2	("5298452").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:46
S22	191	speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:47
S23	1	improve near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 10:49
S24	44	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 11:06
S25	49	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:09
S26	14	("higher" improve improvement improvement increase increasing) near4 speed near4 CMOS near4 (inverter inverter) and (single adj crystal monocrystal monocrystalline)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 11:08
S27	23	"6251751"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:41
S28	18	S27 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42
S29	2	("6251751").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 13:42
S30	1	S29 and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:19
S31	2	("20020125471").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22
S32	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 14:22

S33	1	S31 and (polysilicon polycrystalline poly poly-Si)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:25
S34	28	polycrystalline near4 silicon adj germanium near10 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:26
S35	8	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27
S36	1	polycrystalline near1 silicon adj germanium near4 method.clm. and "438"/\$7.ccls. and thin adj film	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 14:27
S37	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05
S38	2	silicon adj germanium near4 band adj gap near4 wide	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:05
S39	156	silicon adj germanium near4 band adj gap	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:12
S40	37	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:14
S41	10	relaxed near20 strained.clm. and transistor.ti,ab,clm. and (single adj crystal monocrystalline).clm. and silicon and germanium	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/09/07 16:20
S42	4900	((257/76) or (257/213) or (257/288) or (257/347) or (257/350) or (257/351) or (257/616)).CCLS.	US-PGPUB; USPAT	OR	OFF	2005/09/07 16:20
S43	139	S42 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22
S44	16	S42 and relaxed and strained and (Se-Ge Ge-Si (silicon near1 germanium) SiGe "Si.sub."\$4 near1 "Ge.sub."\$4 "Si.sub."\$4 "Ge.sub."\$4 "Ge.sub."\$4 "Si.sub."\$4) and (inverter invertor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2005/09/07 16:22

S45	4	((("6251751") or ("5298452"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 21:18
S46	2	("20020125471").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 22:05
S47	1418	(pfet pmos pmosfet pmisfet) near6 (above below) near6 (nfet nmos nmosfet nmisfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/28 22:06
S48	1480	(pfet pmos pmosfet pmisfet) near6 (above below) near6 (nfet nmos nmosfet nmisfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:06
S49	363	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:07
S50	44	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and (silicon si) near3 (ge germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:07
S51	57	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:08
S52	25	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:09
S53	25	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) and ((silicon si) near3 (ge germanium) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:10
S54	5	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) near4 invert?r and ((silicon si) near3 (ge germanium) sige silicon-germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:12
S55	5	(pfet pmos pmosfet pmisfet) near3 (above below) near3 (nfet nmos nmosfet nmisfet) and (cmos cmosfet) near4 invert?r and (((silicon si) near3 (ge germanium)) sige silicon- germanium) and @ad<"20031004"	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:19

S56	107	stack\$3 near4 (pfet pmos pmosfet pmisfet) near4 (nfet nmos nmosfet nmisfet) and (inverter inverter)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:43
S57	1	"4692994".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:23
S58	1	"3793721".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S59	1	"4467518".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S60	1	"4489478".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:24
S61	1	"4498226".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:25
S62	1	"4502202".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S63	1	"4555843".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S64	1	"4603468".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S65	1	"4649627".PN.	USPAT; USOCR	OR	OFF	2006/01/28 22:26
S66	179	stack\$3 near4 (pfet pmos pmosfet pmisfet) near4 (nfet nmos nmosfet nmisfet)	USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/28 22:43
S67	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2006/01/29 08:25
S68	0	S67 and composition	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 08:25
S69	1	S67 and semiconductor adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 08:25
S70	1	S67 and semiconductor adj layer	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 08:43
S71	252	graded near2 contact	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 08:43
S72	0	graded near2 contact and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S73	0	(grade grading graded) near2 (contact via) and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26

S74	5	(grade grading graded) near2 (contact via interconnect interconnection interconnexion) and (stack stacking stacked) near4 transistor	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 10:26
S75	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2006/01/29 10:51
S76	0	(US-20040145399-\$).did. and (composition composed grade graded grading)	US-PGPUB	OR	ON	2006/01/29 10:52
S77	1	(US-20040145399-\$).did. and (composition composed grade graded grading doping concentration)	US-PGPUB	OR	ON	2006/01/29 11:31
S78	4	cmos adj inverter near6 computer.ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:32
S79	4	cmos adj inverter near20 computer.ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:32
S80	22	cmos adj inverter.ti,ab,clm. and computer.ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:33
S81	0	cmos adj inverter near10 (logic adj circuit).ti,ab,clm. and computer near10 (logic adj circuit).ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:34
S82	0	cmos adj inverter near20 (logic adj circuit).ti,ab,clm. and computer near20 (logic adj circuit).ti,ab,clm.	US-PGPUB	OR	ON	2006/01/29 11:35
S83	10	cmos adj inverter near3 computer	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 11:37
S84	7	cmos adj inverter near6 computer not bhattacharyya.in.	US-PGPUB; USPAT; USOCR; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 11:42
S85	2	("5774008").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 12:10
S86	13	strained near10 relaxed near10 lattice and CMOS near1 invert ?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 13:27
S87	2	("6251751").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:57
S88	6622	((257/76) or (257/213) or (257/288) or (257/347) or (257/350) or (257/351) or (257/616)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:57

S89	2	S88 and (sige silicon adj germanium).ti, ab,clm. and cmos near1 invert?r and (stack stacking stacked) near10 (pfet nfet pmos pmosfet pmisfet nmis nmisfet nmos nmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 13:59
S90	2	S88 and (sige silicon adj germanium).ti, ab,clm. and cmos near1 invert?r and (stack stacking stacked) near10 (pfet nfet pmos pmosfet pmisfet nmis nmisfet nmos nmosfet)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/01/29 14:00
S91	2	("6882010").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/01/29 14:01
S92	2	("6649980").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 16:18
S93	5	"454304".ap.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 16:24
S94	2	"6888750".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 16:25
S95	2	("20030030091").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/06/12 18:27
S96	38	(single adj crystal monocrystalline) near6 relaxed and tensile near4 strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 18:28
S97	36	(single adj crystal monocrystalline) near3 relaxed and tensile near4 strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/06/12 18:28
S98	3	"6800892".pn.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 13:10
S99	6	((("20040179391") or ("20040155317") or ("20040178826"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 15:33
S100	4	stacked adj (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:38

S101	68	(stacking stack stacked) near2 (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:41
S102	10	(stacking stack stacked) near2 (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium) and relaxed near6 strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:42
S103	3	(stacking stack stacked) near2 (TFT thin adj film adj transistor) and (silicon-germanium sige silicon near1 germanium) and (CTE thermal adj expansion)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:46
S104	453	(stacking stack stacked) near2 (TFT thin adj film adj transistor)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:46
S105	101	(stacking stack stacked) near2 (TFT thin adj film adj transistor).ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:50
S106	23110861	(stacking stack stacked) near2 (TFT thin adj film adj transistor)".ti,ab,clm.and"@ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:51
S107	53	(stacking stack stacked) near2 (TFT thin adj film adj transistor).ti,ab,clm. and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 15:54
S108	4	(stacking stack stacked) near2 (TFT thin adj film adj transistor).ti,ab,clm. and @ad<"20021004" and (SiGe si-ge silicon near1 germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 17:14
S111	1	"6888750".pn. and control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/01 19:24
S112	1	"6888750".pn. and control adj gate	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:24
S113	1428	strained and relaxed and (silicon adj germanium sige silicon-germanium)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:25
S114	1085	strained and relaxed and (silicon adj germanium sige silicon-germanium) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:25

S115	64	strained and relaxed and (silicon adj germanium sige silicon-germanium) and (tft thin adj film adj transistor) and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:26
S116	9	strained and relaxed and (silicon adj germanium sige silicon-germanium) and (tft thin adj film adj transistor) and "257"/\$7.ccls. and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:29
S117	9	strained and relaxed and (tft thin adj film adj transistor) and "257"/\$7.ccls. and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:30
S118	13	strained and relaxed and (tft thin adj film adj transistor) and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:31
S119	611	first adj semiconductor adj (film layer) and second adj semiconductor adj (film layer) and (tft thin adj film adj transistor) and @ad<"20021004"	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/01 19:32
S120	0	underfilm near10 (silicon-germanium sige silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 09:11
S121	2	underfilm and (silicon-germanium sige silicon adj germanium germanium adj silicon)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 09:12
S122	0	underfilm and (silicon-germanium sige silicon adj germanium germanium adj silicon) and (tft thin adj film adj transistor "SOI")	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:17
S123	1585	nickel and (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:18
S124	541	nickel near10 catalyst and (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:18
S125	0	nickel near10 catalyst near10 (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:18
S126	2	nickel near10 catalyst with (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 10:19

S127	48	nickel with (silicon-germanium silicon near1 germanium sige) and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:25
S128	918	cmos adj inverter.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:25
S129	45	cmos adj inverter.ti. and "257"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:25
S130	16	cmos adj inverter.ti. and "327"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:26
S131	6	cmos adj inverter.ti. and "365"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2006/11/02 11:26
S132	44	cmos adj inverter.ti.	USPAT	OR	ON	2006/11/02 11:28
S133	7740	((257/65) or (257/66) or (257/69) or (257/213) or (257/288) or (257/350) or (257/351) or (257/616) or (326/121)). CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:29
S134	3	S133 and (silicon-germanium silicon near1 germanium sige) and (invert?r near1 CMOS) and (composition compositional compositionally) and stack \$3 near1 (transistor tft mosfet mos)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:33
S135	58	bhattacharyya.in. and tft and germanium	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:38
S136	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2).clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and nfet.clm. and pfet.clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:42
S137	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2).clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and (tft nfet).clm. and (tft pfet).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:43

S138	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2).clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and (tft thin adj film adj transistor nfet).clm. and (tft thin adj film adj transistor pfet).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:43
S139	0	(bhattacharyya.in. micron.as.) and (composition compositional\$2).clm. and (germanium near1 silicon silicon-germanium sige).clm. and invert?1r.clm. and first near3 (layer film).clm. and second near3 (layer film).clm. and (tft thin adj film adj transistor nfet pfet).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2006/11/02 11:48
S140	40	((("4333808") or ("4488262") or ("4648179") or ("4870470") or ("4776922") or ("5811870") or ("5874778") or ("6344373") or ("7012297") or ("6700771") or ("6933572") or ("6743681") or ("6784480") or ("7132348") or ("6943065") or ("6828632") or ("6903001") or ("6917078") or ("6903969") or ("7042027") or ("6759712") or ("6873015") or ("6998683") or ("6882010") or ("6768156") or ("6800892") or ("6812504") or ("7042052") or ("6713810") or ("7026690") or ("6998667") or ("6845034") or ("6900667") or ("6888200") or ("6908798") or ("6873018") or ("6955960") or ("6982457") or ("7130216") or ("7019378") or ("6950340"))).PN.	USPAT; JPO	OR	OFF	2006/11/02 12:20
S141	0	("20030030091").PN.	USPAT; JPO	OR	OFF	2006/11/02 15:19
S142	1	("20030030091").PN.	US-PGPUB; USPAT; JPO	OR	OFF	2006/11/02 12:20
S143	0	("20030030091").PN.	USPAT; JPO	OR	OFF	2006/11/02 15:19
S144	2	("6888750").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 12:51
S145	0	("tftnear4flash").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 12:51
S146	37	tft near4 flash	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:14

S147	2	("6882010").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:14
S148	8022	((257/65) or (257/66) or (257/69) or (257/213) or (257/288) or (257/350) or (257/351) or (257/616) or (326/121)). CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:23
S149	23	S148 and invert?r and drain and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS) and relaxed and strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:37
S150	11	((bhattacharyya near3 arup).in. micron. as.) and invert?r.clm. and drain.clm. and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS).clm. and relaxed and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:27
S151	5	((bhattacharyya near3 arup).in. micron. as.) and invert?r.clm. and drain.clm. and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS).clm. and signal. clm. and relaxed and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:35
S152	5	((bhattacharyya near3 arup).in. micron. as.) and invert?r.clm. and drain.clm. and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS).clm. and signal. clm. and insulat\$3.clm. and relaxed and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/03/17 13:37
S153	5	((bhattacharyya near3 arup).in. micron. as.) and invert?r.clm. and drain.clm. and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS).clm. and signal. clm. and insulat\$3.clm. and relaxed and strain\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 13:37
S154	23	S148 and invert?r and drain and (field adj effect adj transistor FET PFET NFET NMOSFET PMOSFET NMISFET PMISFET NMOS PMOS) and relaxed and strained	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/03/17 13:37
S155	17073	nand adj gate near6 invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/16 14:26
S156	12968	nand adj gate near3 invert?r	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:26
S157	1879	nand adj gate near3 invert?r.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:26

S158	540	nand adj gate near1 invert?r.ti,ab,clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:26
S159	94	nand adj gate near1 invert?r.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:27
S160	3604	nand adj gate.ti.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/16 14:33
S161	2	("6888750").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/16 14:33
S162	2	("6888750").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/18 15:12
S163	0	("inverternear4 (flashadjmemoryadjarray)").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/18 15:12
S164	1	flash adj memory adj array near6 inverter	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/05/18 15:16
S165	1110	eeeprom near4 cmos	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/18 15:24
S166	47	eeeprom near4 cmos and tft	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/05/18 15:24
S167	4	((("6888750") or ("6759677"))).PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/18 08:27
S168	2	("6882010").PN.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/18 08:27
S169	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2007/08/18 11:39
S170	0	(US-20040145399-\$).did. and (overlap overlapping non-overlap non- overlapping)	US-PGPUB	OR	OFF	2007/08/18 11:40

S171	1	(US-20040145399-\$).did. and (overlap overlapping non-overlap non-overlapping)	US-PGPUB	OR	ON	2007/08/18 11:40
S172	1	(US-20040145399-\$).did. and (overlap overlapping non-overlap non-overlapping island)	US-PGPUB	OR	ON	2007/08/18 11:41
S173	1	(US-20040145399-\$).did.	US-PGPUB	OR	OFF	2007/08/18 14:56
S174	1	(US-20040145399-\$).did. and (self-alignment self\$1alignment self\$1align self\$1aligning align\$4 overlap\$4 non\$1overlap\$4)	US-PGPUB	OR	ON	2007/08/18 15:17
S175	8429	("0257213").PN. or ((257/65) or (257/66) or (257/69) or (257/288) or (257/350) or (257/351) or (257/616) or (326/121) or (257/903)).CCLS.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2007/08/18 15:18
S176	2	S175 and (inverter invertor) and (PFET PMOS PMOSFET PMISFET) and (germanium Ge) and (stack\$3 near10 (transistor MOS MOSFET MIS MISFET TFT CMOS CMOSFET)) and (self-alignment self-align self\$1alignment self\$1align self near1 (align alignment))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/18 15:22
S177	0	(arup near1 bhattacharyya).in. and (inverter invertor) and (PFET PMOS PMOSFET PMISFET) and (germanium Ge) and (stack\$3 near10 (transistor MOS MOSFET MIS MISFET TFT CMOS CMOSFET)) and (self-alignment self-align self\$1alignment self\$1align self near1 (align alignment))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/18 15:23
S178	0	(arup near1 bhattacharyya).in. and (inverter invertor).clm. and (PFET PMOS PMOSFET PMISFET).clm. and (germanium Ge).clm. and (self-alignment self-align self\$1alignment self\$1align alignment aligned align non\$1overlap non\$1overlapping overlap\$4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/18 15:25
S179	0	((arup near1 bhattacharyya).in. micron. as.) and (inverter invertor).clm. and (PFET PMOS PMOSFET PMISFET).clm. and (germanium Ge).clm. and (self-alignment self-align self\$1alignment self\$1align alignment aligned align non\$1overlap non\$1overlapping overlap\$4).clm.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2007/08/18 15:25
S180	0	physical adj contact near3 instead near3 (electrical adj contact)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/18 11:24
S181	7	((("6888750") or ("6693044") or ("6759677")).PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/18 12:14

S182	1	"709995".ap. and kinetic adj energy	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/18 14:56
S183	2	("6,888750").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/19 09:55
S184	1	S183 and pillar	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 09:56
S185	2	bhattacharyya.in. and mondt.xa.xp.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 10:29
S186	0	S183 and pillar near20 (electrical\$1 physical\$1 connect\$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 10:40
S187	1	(US-20040145399-\$).did.	US-PGPUB	OR	ON	2008/03/19 14:14
S188	1	structure and S187	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 14:14
S189	1	(US-20040145399-\$).did. and relaxed near10 "16"	US-PGPUB	OR	ON	2008/03/19 14:40
S190	1	(US-20040145399-\$).did. and ("100" and "122")	US-PGPUB	OR	ON	2008/03/19 15:55
S191	1	(US-20040145399-\$).did. and (comprising near4 silicon near4 germanium)	US-PGPUB	OR	ON	2008/03/19 15:58
S192	1	(US-20040145399-\$).did. and (compris \$3 near4 (Si silicon) near4 (Ge germanium))	US-PGPUB	OR	ON	2008/03/19 16:05
S193	1	(US-20040145399-\$).did. and (structure)	US-PGPUB	OR	ON	2008/03/19 16:23
S194	1	(US-20040145399-\$).did. and (crystalline adj structure)	US-PGPUB	OR	ON	2008/03/19 16:57
S195	1	(US-20040145399-\$).did. and (inverter adj structure)	US-PGPUB	OR	ON	2008/03/19 16:59
S196	1	(US-20040145399-\$).did. and ("122")	US-PGPUB	OR	ON	2008/03/19 17:11

S197	8952	((257/65) or (257/66) or (257/69) or (257/213) or (257/288) or (257/350) or (257/351) or (257/616) or (326/121)). CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/19 18:26
S198	59	S197 and invert?r.ti,ab,clm. and (field adj effect adj transistor FET) and (stack\$3 pillar)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 18:29
S199	197	S197 and (CMOS CMOSFET SRAM invert? r).ti,ab,clm. and (field adj effect adj transistor FET) and (stack\$3 pillar)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/19 18:30
S200	8959	((257/65) or (257/66) or (257/69) or (257/213) or (257/288) or (257/350) or (257/351) or (257/616) or (326/121)). CCLS.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/20 08:19
S201	36	S200 and (CMOS CMOSFET SRAM invert? r).ti,ab,clm. and (field adj effect adj transistor FET) and (stack\$3 pillar) and (Si silicon).clm. and (Ge germanium). clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 08:19
S202	1	(US-20040145399-\$).did.	US-PGPUB	OR	ON	2008/03/20 09:05
S203	1	(US-20040145399-\$).did. and (single adj crystal crystalline mono\$1crystalline mono\$1crystal)	US-PGPUB	OR	ON	2008/03/20 09:06
S204	432	sram and (non\$1overlapping self \$1aligned self\$1alignment) near4 (gate source drain)	US-PGPUB	OR	ON	2008/03/20 09:14
S205	0	sram and (non\$1overlapping self \$1aligned self\$1alignment) near4 (gate source drain) and (first adj conductivity near10 second adj conductivity near10 n-type near10 p-type near10 interchangeable)	US-PGPUB	OR	ON	2008/03/20 09:15
S206	0	sram and (non\$1overlapping self \$1aligned self\$1alignment) near4 (gate source drain) and (first adj conductivity near10 second adj conductivity near10 n-type near10 p-type)	US-PGPUB	OR	ON	2008/03/20 09:15
S207	0	sram and (non\$1overlapping self \$1aligned self\$1alignment) near4 (gate source drain) and (first adj conductivity near20 second adj conductivity near20 n-type near20 p-type)	US-PGPUB	OR	ON	2008/03/20 09:16
S208	432	sram and (non\$1overlapping self \$1aligned self\$1alignment) near4 (gate source drain)	US-PGPUB	OR	ON	2008/03/20 09:18
S209	557	sram and (non\$1overlapping self \$1aligned self\$1alignment) near4 (gate source drain)	US-PGPUB	OR	ON	2008/03/20 09:18

S210	0	sram and (non\$1overlapping self\$1aligned self\$1alignment) near4 (gate source drain) and (first adj conductivity near20 second adj conductivity near20 n-type near20 p-type)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 09:18
S211	335	sram.ti,ab,clm. and (non\$1overlapping self\$1aligned self\$1alignment) near4 (gate source drain)/ti,ab,clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 09:21
S212	109	sram.ti,ab,clm. and (non\$1overlapping self\$1aligned self\$1alignment) near4 (gate source drain).ti,ab,clm.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 09:22
S213	97	sram.ti,ab,clm. and (non\$1overlapping self\$1aligned self\$1alignment) near4 (gate source drain).ti,ab,clm. and @ad< "20040115"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 09:23
S214	36	sram.ti,ab,clm. and (non\$1overlapping self\$1aligned self\$1alignment) near4 (gate source drain).ti,ab,clm. and @ad< "20040115" and (stack stacked stacking)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 09:24
S215	1	(US-20040145399-\$).did. and strained near6 silicon near6 germanium	US-PGPUB	OR	ON	2008/03/20 09:43
S216	0	WO-96030936\$-\$\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 10:21
S217	0	WO-960030936\$-\$\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 10:22
S218	0	ep-96906603\$-\$\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 10:24
S219	0	ep-960906603\$-\$\$.did.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 10:24

S220	0	(self\$1alignment self\$aligned self\$1aligning self\$1align).ti. and process.ti. and tft adj eeprom	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 10:25
S221	20	(self\$1alignment self\$aligned self\$1aligning self\$1align).ti. and process.ti. and tft	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 10:26
S222	2	(self\$1alignment self\$aligned self\$1aligning self\$1align).ti. and process.ti. and tft and (self\$1alignment self\$aligned self\$1aligning self\$1align) near10 (cost efficiency precision accuracy)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 10:28
S223	68	compact near6 mixture and uranium and aluminum	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 11:11
S224	8	compact near6 mixture near6 uranium and aluminum	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 11:11
S225	37428	compact near6 (heat pressure pressu? \$3)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 11:16
S226	37311	compact near6 (heat pressure)	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 11:16
S227	295	compact near6 (heat pressure) and uranium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 11:16
S228	15	compact near6 (heat pressure) near6 uranium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 11:17
S229	22	compact near6 (formation forming) near6 uranium	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 11:18

S230	3	("3288571").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/20 11:26
S231	2	S230 and compact	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 11:26
S232	3	("3288571").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/20 11:27
S233	2	S232 and compact	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 11:27
S234	1	(US-20040145399-\$).did.	US-PGPUB	OR	ON	2008/03/20 12:18
S235	1	S234 and "116"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 12:19
S236	2	("6888750").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/20 12:19
S237	1	S236 and "116"	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2008/03/20 12:19
S238	3	("6,759,677").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/20 13:39
S239	2	("6,693,044").PN.	US-PGPUB; USPAT; USOCR; FPRS; EPO; JPO; DERWENT; IBM_TDB	OR	OFF	2008/03/20 13:45

3/20/2008 3:50:29 PM

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